

TIC226A, TIC226B, TIC226C, TIC226D, TIC226E, TIC226M, TIC226N, TIC226S

SILICON BIDIRECTIONAL TRIODE THYRISTOR

- 8 A RMS
- 70 A Peak
- Glass Passivated Wafer
- 100 V to 800 V Off-State Voltage
- Max I_{GT} of 50 mA (Quadrants 1-3)
- High-temperature, High-current and high-voltage applications
- Compliance to ROHS

DESCRIPTION

This device is a bidirectional triode thyristor (triac) which may be triggered from the off-state to the on-state by either polarity of gate signal with main Terminal 2 at either polarity.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value								Unit
		A	B	C	D	E	M	S	N	
V_{DRM}	Repetitive peak off-state voltage (see Note1)	100	200	300	400	500	600	700	800	V
$I_{T(RMS)}$	Full-cycle RMS on-state current at (or below) 70°C case temperature (see note2)	8								A
I_{TSM}	Peak on-state surge current full-sine-wave (see Note3)	70								A
I_{TSM}	Peak on-state surge current half-sine-wave (see Note4)	8								A
I_{GM}	Peak gate current	± 1								A
P_{GM}	Peak gate power dissipation at (or below) 85°C case temperature (pulse width $\leq 200 \mu s$)	2.2								W
$P_{G(AV)}$	Average gate power dissipation at (or below) 85°C case (see Note5)	0.9								W
T_C	Operating case temperature range	-40 to +110								°C
T_{stg}	Storage temperature range	-40 to +125								°C
T_L	Lead temperature 1.6 mm from case for 10 seconds	230								°C

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THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
$R_{\theta JC}$	Junction to case thermal resistance	≤ 1.8	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Junction to free air thermal resistance	≤ 62.5	

ELECTRICAL CHARACTERISTICS

$T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
I_{DRM}	Repetitive peak off-state current	$V_D = \text{Rated } V_{DRM}, I_G = 0$ $T_C = 110^{\circ}\text{C}$	-	-	± 2	mA
I_{GT}	Gate trigger current	$V_{supply} = +12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	2	50	mA
		$V_{supply} = +12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	-12	-50	
		$V_{supply} = -12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	-9	-50	
		$V_{supply} = -12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	20	-	
V_{GT}	Gate trigger voltage	$V_{supply} = +12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	0.7	2	V
		$V_{supply} = +12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	-0.8	-2	
		$V_{supply} = -12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	-0.8	-2	
		$V_{supply} = -12\text{ V}\dagger, R_L = 10\ \Omega, t_{p(g)} = > 20\ \mu\text{s}$	-	0.9	2	
I_H	Holding current	$V_{supply} = +12\text{ V}\dagger, I_G = 0$ initiating $I_{TM} = 100\text{ mA}$	-	5	30	mA
		$V_{supply} = -12\text{ V}\dagger, I_G = 0$ initiating $I_{TM} = -100\text{ mA}$	-	-9	-30	
I_L	Latching current	$V_{supply} = +12\text{ V}\dagger$ (see Note 7)	-	-	50	mA
		$V_{supply} = -12\text{ V}\dagger$ (see Note 7)	-	-	-50	
V_{TM}	Peak on-state voltage	$I_{TM} = \pm 12\text{ A}, I_G = 50\text{ mA}$ (see Note 6)	-	± 1.6	± 2.1	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DRM} = \text{Rated } V_{DRM}, I_G = 0$ $T_C = 110^{\circ}\text{C}$	-	± 100	-	V/ μs
$dv/dt_{\odot}$	Critical rise of communication voltage	$V_{DRM} = \text{Rated } V_{DRM}, I_{TRM} = \pm 12\text{ A}$ $T_C = 85^{\circ}\text{C}$	± 5	-	-	

$\dagger$ All voltages are with respect to Main Terminal 1.

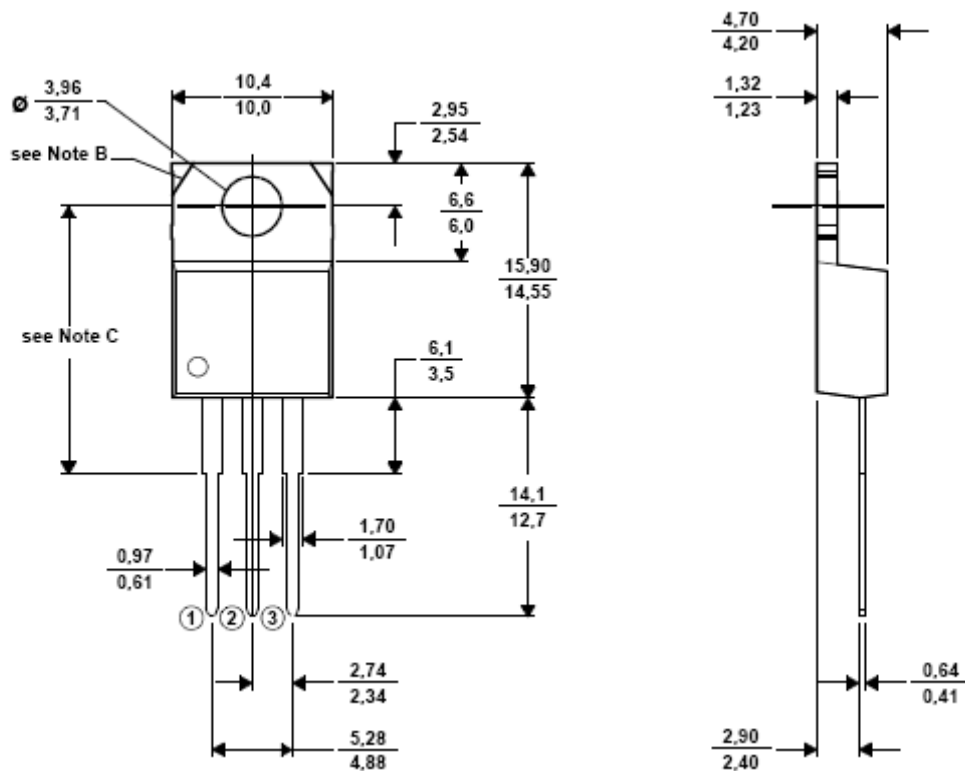
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Notes:

1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 320 mA/°C.
3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
5. This value applies for a maximum averaging time of 20 ms.
6. This parameters must be measured using pulse techniques, $t_w = \leq 1\text{ms}$, duty cycle $\leq 2\%$, voltage-sensing contacts, separate from the current-carrying contacts are located within 3.2mm (1/8 inch) from the device body.
7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics : $R_G = 100\Omega$, $t_{p(g)} = 20\ \mu\text{s}$, $t_r = \leq 15\text{ns}$, $f = 1\text{ kHz}$.

MECHANICAL DATA CASE TO-220

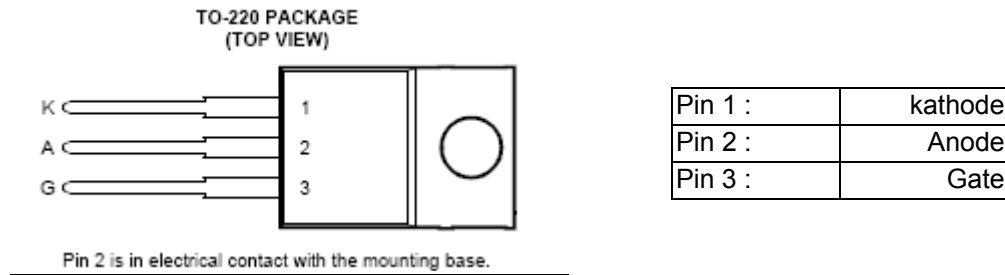
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PINNING



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